



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790DAGeneric Copy

Issue Date: 23-Jul-2012

TITLE: Final PCN for wafer fab transfer from Gifu to the waferfab United Microelectronics Corporation Japan (UMCJ).(Group DA).

PROPOSED FIRST SHIP DATE: starting on 15 Oct 2012 until 30 Oct 2012 (the actual ship date will be different by each product, please check the responsible Sales person).

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Location Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Toshikazu.Hirai@onsemi.com

SAMPLES: Contact your local ON Semiconductor Sales Office or Akira.Yoneyama@onsemi.com

ADDITIONAL RELIABILITY DATA: May be available

Contact your local ON Semiconductor Sales Office or Yasuhiro.Igarashi@onsemi.com.

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>

DESCRIPTION AND PURPOSE:

This is a Final Process Change Notification to announce the transfer of products from Sanyo wafer fabrication sites located in Gifu to the waferfab United Microelectronics Corporation Japan (UMCJ).

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790DA****QUALIFICATION PLAN:**

Estimated Date for Qualification Completion: starting on January 2012 until March 2012, dependent of the process/product.

Samples should be available after completion of Qualification.

RELIABILITY DATA SUMMARY**Group DA**

Test:	Conditions:	Interval:	Results
High Temperature Storage	Ta=150degC	1000 hrs	Pass
Low Temperature Storage	Ta=-55degC	1000 hrs	Pass
Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass
Steady State Operating Life	Tj=150degC	1000 hrs	Pass
High Temperature Reverse Bias	Ta=150degC, VDSS=24V	1000 hrs	Pass
Temperature Cycle	Ta=-55degC to 150degC 30min each	100 cycles	Pass
Pressure Cooker	Ta=121degC, 2.03 × 10 ⁵ Pa, 100%	50 hrs	Pass
Resistance to Soldering heat	Solder Temp: 26.0 ± 5degC	10 s	Pass
Solder ability	Ta=245 ± 5degC	5 s	Pass

Notice) ※1 Pre-treatment: Resistance to Soldering heat (Flow: 260degC/10s)

ELECTRICAL CHARACTERISTIC SUMMARY

No change to the device data sheets is being made. All parametric performance and limits remain the same.

CHANGED PART IDENTIFICATION

No change to current part making will occur. Making traceability codes will be able to identify wafer fab die source.

List of affected Generic parts:**Group DA**

PART_ID
ECH8601M-TL-H
ECH8651R-TL-H